TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

## GT30J324

## High Power Switching Applications

Fast Switching Applications

- The 4th generation
- Enhancement-mode
- Fast switching (FS): Operating frequency up to 50 kHz (reference) High speed: $\mathrm{tf}_{\mathrm{f}}=0.05 \mu \mathrm{~s}$ (typ.)
Low switching loss: Eon $=1.00 \mathrm{~mJ}$ (typ.) : E off $=0.80 \mathrm{~mJ}$ (typ.)
- Low saturation voltage: VCE (sat) $=2.0 \mathrm{~V}$ (typ.)
- FRD included between emitter and collector

Maximum Ratings $\left(\mathbf{T a}=25^{\circ} \mathrm{C}\right)$

| Characteristics |  | Symbol | Rating | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Collector-emitter voltage |  | $V_{\text {CES }}$ | 600 | V |
| Gate-emitter voltage |  | $V_{\text {GES }}$ | $\pm 20$ | V |
| Collector current | DC | $l_{C}$ | 30 | A |
|  | 1 ms | $\mathrm{I}_{\mathrm{CP}}$ | 60 |  |
| Emitter-collector forward current | DC | $\mathrm{I}_{\mathrm{F}}$ | 30 | A |
|  | 1 ms | $\mathrm{I}_{\text {FM }}$ | 60 |  |
| Collector power dissipation ( $\mathrm{Tc}=25^{\circ} \mathrm{C}$ ) |  | $\mathrm{P}_{\mathrm{C}}$ | 170 | W |
| Junction temperature |  | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature range |  | $\mathrm{T}_{\text {stg }}$ | -55 to 150 | ${ }^{\circ} \mathrm{C}$ |

Unit: mm


Weight: 4.6 g (typ.)

## Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Thermal resistance (IGBT) | $R_{\text {th }(\mathrm{j}-\mathrm{c})}$ | 0.735 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal resistance (diode) | $\mathrm{R}_{\text {th }}(\mathrm{j}-\mathrm{c})$ | 1.90 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Equivalent Circuit



Electrical Characteristics ( $\mathrm{Ta}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Characteristics |  | Symbol | Test Condition | Min | Typ. | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Gate leakage current |  | IGES | $\mathrm{V}_{\mathrm{GE}}= \pm 20 \mathrm{~V}, \mathrm{~V}_{\mathrm{CE}}=0$ | - | - | $\pm 500$ | nA |
| Collector cut-off current |  | ICES | $\mathrm{V}_{\mathrm{CE}}=600 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=0$ | - | - | 1.0 | mA |
| Gate-emitter cut-off voltage |  | $\left.\mathrm{V}_{\text {GE ( }} \mathrm{OFF}\right)$ | $\mathrm{I}_{\mathrm{C}}=3 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=5 \mathrm{~V}$ | 3.5 | - | 6.5 | V |
| Collector-emitter saturation voltage |  | $\mathrm{V}_{\text {CE (sat) }}$ | $\mathrm{I}_{\mathrm{C}}=30 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}$ | - | 2.0 | 2.45 | V |
| Input capacitance |  | Cies | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=0, \mathrm{f}=1 \mathrm{MHz}$ | - | 4650 | - | pF |
| Switching time | Turn-on delay time | $\mathrm{t}_{\mathrm{d}}$ (on) | Inductive Load$\left\{\begin{array}{l} \mathrm{V}_{\mathrm{CC}}=300 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=30 \mathrm{~A} \\ \mathrm{~V}_{\mathrm{GG}}=+15 \mathrm{~V}, \mathrm{R}_{\mathrm{G}}=24 \Omega \end{array}\right.$ | - | 0.09 | - | $\mu \mathrm{s}$ |
|  | Rise time | $t_{r}$ |  | - | 0.07 | - |  |
|  | Turn-on time | $t_{\text {on }}$ |  | - | 0.24 | - |  |
|  | Turn-off delay time | $\mathrm{t}_{\mathrm{d}}$ (off) |  | - | 0.30 | - |  |
|  | Fall time | $t_{f}$ |  | - | 0.05 | - |  |
|  | Turn-off time | $t_{\text {off }}$ |  | - | 0.43 | - |  |
| Switching loss | Turn-on switching loss | $E_{\text {on }}$ |  | - | 1.00 | - | mJ |
|  | Turn-off switching loss | $\mathrm{E}_{\text {off }}$ |  | - | 0.80 | - |  |
| Peak forward voltage |  | $V_{F}$ | $\mathrm{I}_{\mathrm{F}}=30 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=0$ | - | - | 3.8 | V |
| Reverse recovery time |  | $\mathrm{trr}^{\text {r }}$ | $\mathrm{I}_{\mathrm{F}}=30 \mathrm{~A}, \mathrm{di} / \mathrm{dt}=-100 \mathrm{~A} / \mu \mathrm{s}$ | - | 60 | - | ns |

Note 1: Switching time measurement circuit and input/output waveforms


Note 2: Switching loss measurement waveforms














Safe Operating Area




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